NTE620
Silicon Rectifier, General Purpose, High Voltage, Standard Recovery
DO−213AA Surface Mount Type Case

Features:

- High Temperature Metallurgically Bonded
- Glass Passivated Junction
- High Temperature Soldering Guaranteed:
  +450°C/5 Seconds at Terminals. Complete Device Submersible Temperature of +260°C/10 Seconds in Solder Bath.
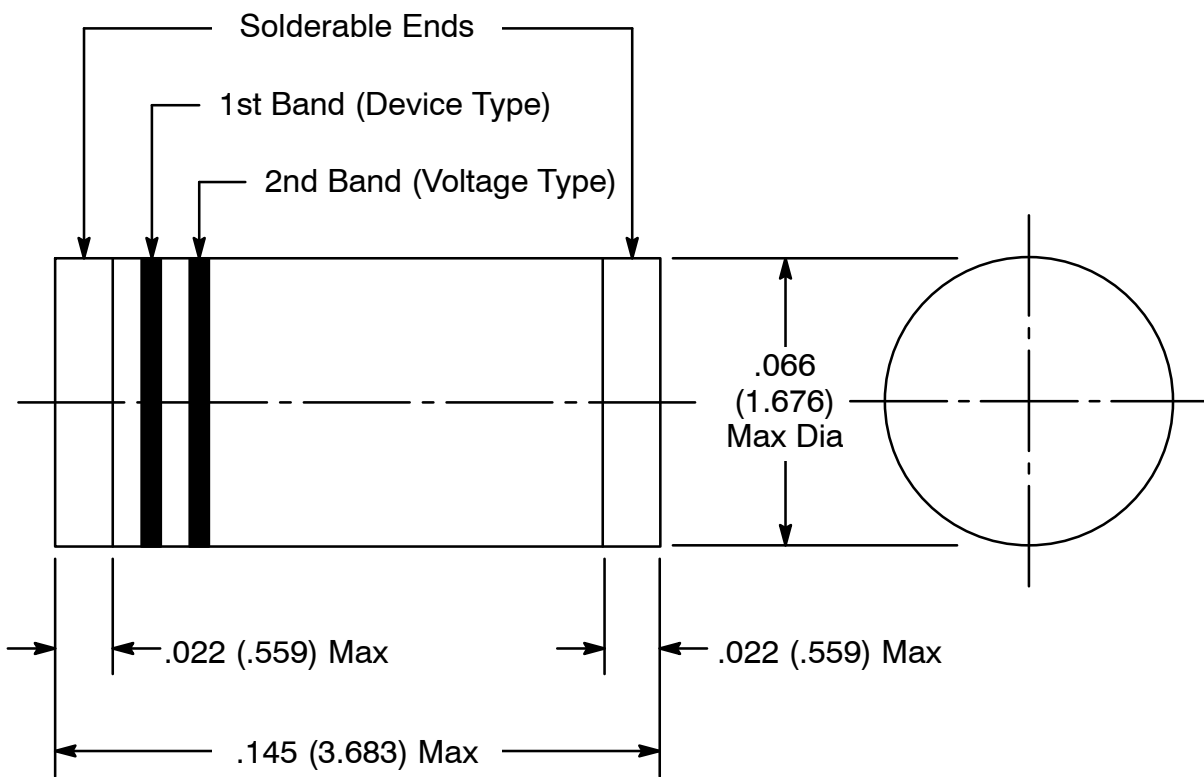
Maximum Ratings and Electrical Characteristics: (T_A = +25°C unless otherwise specified. 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

Maximum Recurrent Peak Reverse Voltage, V_{RRM} 400V

Maximum RMS Voltage, V_{RMS} 280V

Maximum DC Blocking Voltage, V_{DC} 400V

Maximum Average Forward Rectified Current (T_T = +75°C), $I_{T(AV)}$ 0.5A

Peak Forward Surge Current, I_{FSM}
    (8.3ms Single Half Sine−Wave Superimposed on Rated Load) 10A

Maximum Instantaneous Forward Voltage (I_T = 0.5A), V_F 1.2V

Maximum DC Reverse Current (V_{DC} = 400V), I_R
    T_A = +25°C . . . . 5 A
    T_A = +125°C . . . . 50 A

Maximum Full Load Reverse Current (Full Cycle Average at T_A = +75°C), $I_{R(AV)}$ . . . . 20 A

Typical Junction Capacitance (Note 1), C_J 7pF

Operating Junction Temperature Range, T_J . . . . −65° to +175°C

Storage Temperature Range, T_{stg} . . . . −65° to +175°C

Maximum Thermal Resistance, Junction−to−Terminal (Note 2), R_{thJL} . . . . 70°C/W

Maximum Thermal Resistance, Junction−to−Ambient (Note 3), R_{thJA} . . . . 150°C/W

Note 1. Measured at 1MHz and applied reverse voltage of $4V_{DC}$.

Note 2. Thermal resistance, junction−to−terminal, 5.0mm^2 copper pads to each terminal.

Note 3. Thermal resistance, junction−to−ambient, 5.0mm^2 copper pads to each terminal.

Solderable Ends

1st Band (Device Type)

2nd Band (Voltage Type)

.066
(1.676)
Max Dia

.022 (.559) Max

.022 (.559) Max

.145 (3.683) Max

Two Bands Indicates Cathode